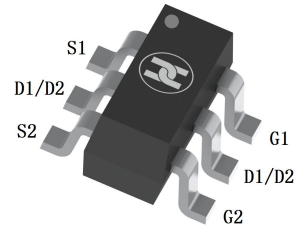
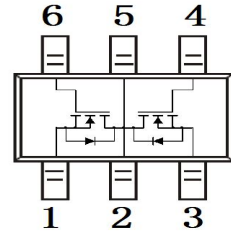


**Dual N-Channel Enhancement Mode Field Effect Transistor**
**FEATURES**

- Low on-resistance:  $V_{DS}=20V, I_D=5A, R_{DS(ON)} \leq 25m\Omega @ V_{GS}=4.5V$
- Low gate charge
- For synchronous rectifier applications
- Surface Mount device


**SOT-23-6**

**MECHANICAL DATA**

- Case: SOT-23-6
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.3 grams (approximate)
- Marking: 8205A

**MAXIMUM RATINGS ( $T_A = 25^\circ C$  unless otherwise noted)**

| Parameter                                     | Symbol          | Value      | Unit         |
|---|-----------------|------------|--------------|
| Drain-source voltage                          | $V_{DS}$        | 20         | V            |
| Gate-source voltage                           | $V_{GS}$        | $\pm 12$   | V            |
| Continuous drain current @ $T_A = 25^\circ C$ | $I_D$           | 5          | A            |
| Pulsed drain current                          | $I_{DM}$        | 25         | A            |
| Power dissipation                             | $P_D$           | 1.25       | W            |
| Thermal resistance from Junction to ambient   | $R_{\theta JA}$ | 100        | $^\circ C/W$ |
| Junction and Storage temperature Range        | $T_J, T_{STG}$  | -55 ~ +150 | $^\circ C$   |

**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ C$  unless otherwise specified)**

| Parameter                                 | Symbol          | Min  | Typ  | Max       | Unit       | Conditions   |
|---|-----------------|------|------|-----------|------------|--|
| <b>STATIC CHARACTERISTICS</b>             |                 |      |      |           |            |  |
| Drain-Source breakdown voltage            | $V_{(BR)DSS}^*$ | 20   |      |           | V          | $V_{GS}=0V, I_D=250\mu A$  |
| Zero gate voltage drain current           | $I_{DSS}^*$     |      |      | 1         | $\mu A$    | $V_{DS}=20V, V_{GS}=0V$  |
| Gate-body leakage current                 | $I_{GSS}^*$     |      |      | $\pm 100$ | nA         | $V_{DS}=0V, V_{GS}=\pm 12V$  |
| Gate-threshold voltage                    | $V_{GS(th)}^*$  | 0.4  | 0.62 | 1.0       | V          | $V_{DS}=V_{GS}, I_D=250\mu A$                                      |
| Drain-source on-resistance                | $R_{DS(ON)}^*$  |      | 18.5 | 25        | m $\Omega$ | $V_{GS}=4.5V, I_D=4A$  |
|   |                 |      | 25.5 | 34        | m $\Omega$ | $V_{GS}=2.5V, I_D=3A$  |
| Forward transconductance                  | $g_{FS}$        |      | 13   |           | S          | $V_{DS}=5V, I_D=5A$  |
| <b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> |                 |      |      |           |            |  |
| Diode forward voltage                     | $V_{SD}$        | 0.42 |      | 1.28      | V          | $I_S=1.7A, V_{GS}=0V$  |
| <b>DYNAMIC CHARACTERISTICS</b>            |                 |      |      |           |            |  |
| Input capacitance                         | $C_{iss}$       |      | 800  |           | pF         | $V_{DS}=8V, V_{GS}=0V, f=1MHz$                                     |
| Output capacitance                        | $C_{oss}$       |      | 155  |           | pF         |  |
| Reverse transfer capacitance              | $C_{rss}$       |      | 125  |           | pF         |  |
| <b>SWITCHING CHARACTERISTICS</b>          |                 |      |      |           |            |  |
| Total gate charge                         | $Q_g$           |      | 11   |           | nC         | $V_{GS}=4V, V_{DS}=10V, I_D=4A$                                    |
| Gate-source charge                        | $Q_{gs}$        |      | 2.2  |           | nC         |  |
| Gate-drain charge                         | $Q_{gd}$        |      | 2.5  |           | nC         |  |
| Turn-on delay time                        | $t_{d(on)}$     |      | 18.3 |           | nS         | $V_{DD}=10V, I_D=1.0A, V_{GEN}=4V, R_{GEN}=10\Omega, R_L=10\Omega$ |
| Turn-on rise time                         | $t_r$           |      | 4.8  |           | nS         |  |
| Turn-off delay time                       | $t_{d(off)}$    |      | 43.5 |           | nS         |  |
| Turn-off fall time                        | $t_f$           |      | 20   |           | nS         |  |

\*Pulse test ; Pulse width < 300 $\mu s$ , Duty cycle  $\leq 2\%$  .

**Dual N-Channel Enhancement Mode Field Effect Transistor**

**Typical Characteristics**

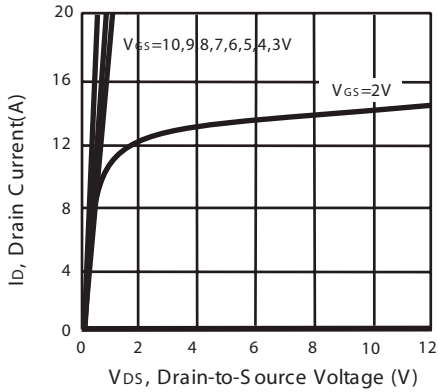


Figure 1. Output Characteristics

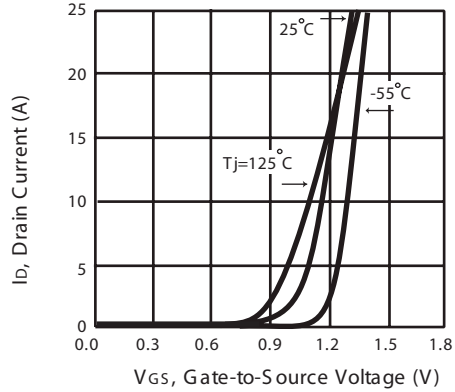


Figure 2. Transfer Characteristics

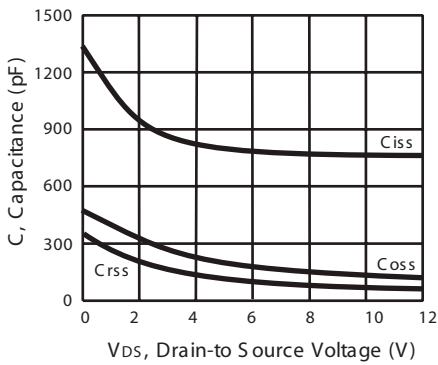


Figure 3. Capacitance

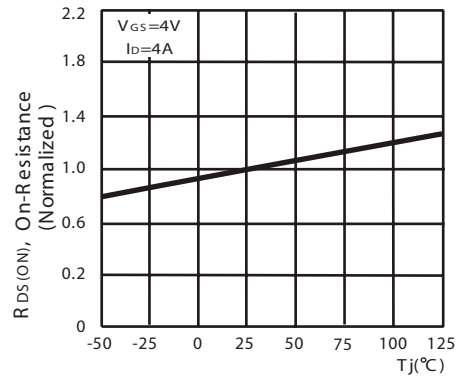


Figure 4. On-Resistance Variation with Temperature

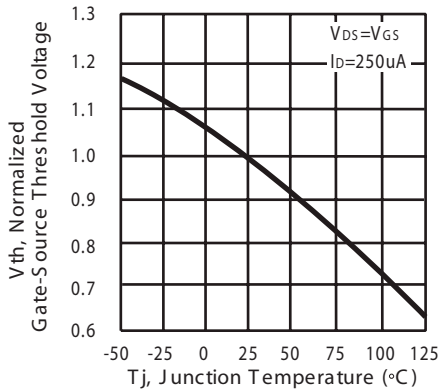


Figure 5. Gate-Source Threshold Voltage with Temperature

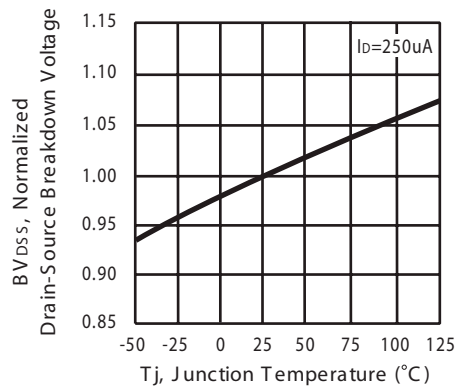


Figure 6. Breakdown Voltage Variation with Temperature

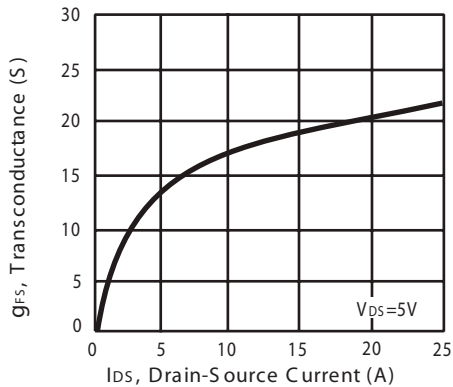


Figure 7. Transconductance Variation with Drain Current

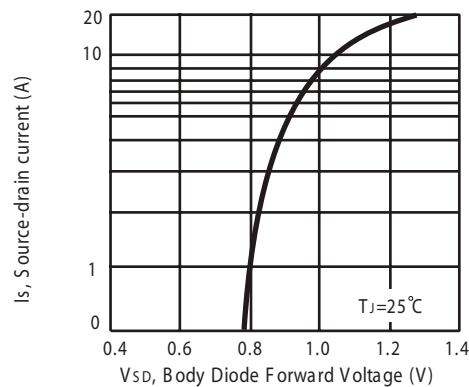


Figure 8. Body Diode Forward Voltage Variation with Source Current

**Dual N-Channel Enhancement Mode Field Effect Transistor**

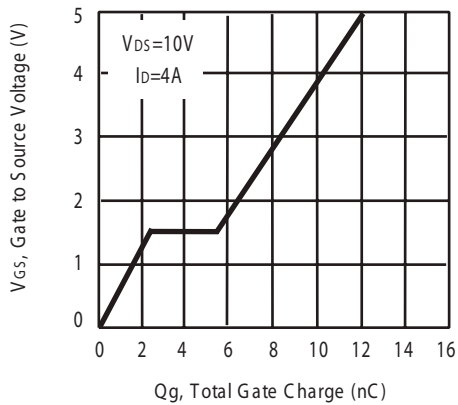


Figure 9. Gate Charge

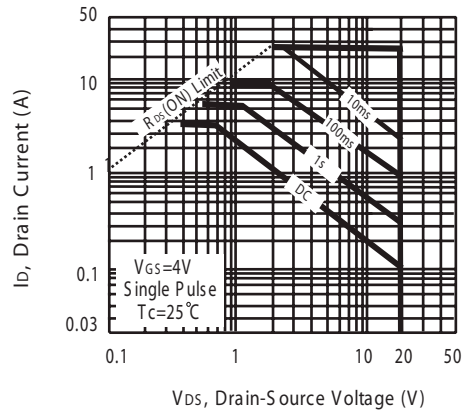


Figure 10. Maximum Safe Operating Area

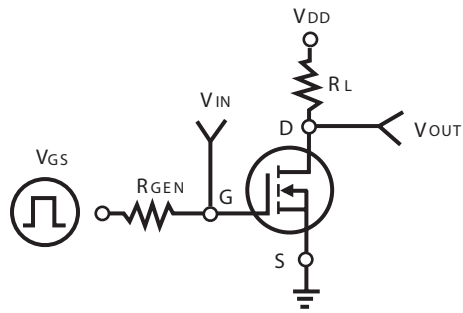


Figure 11. S switching Test Circuit

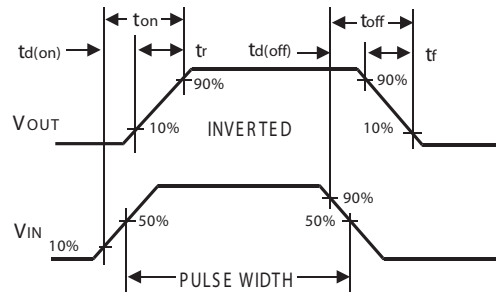
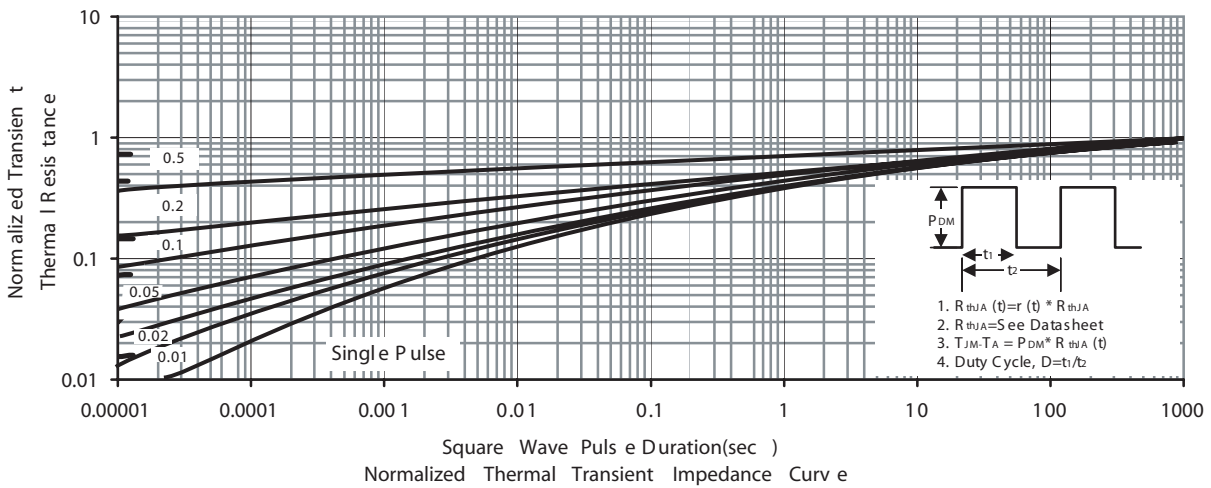
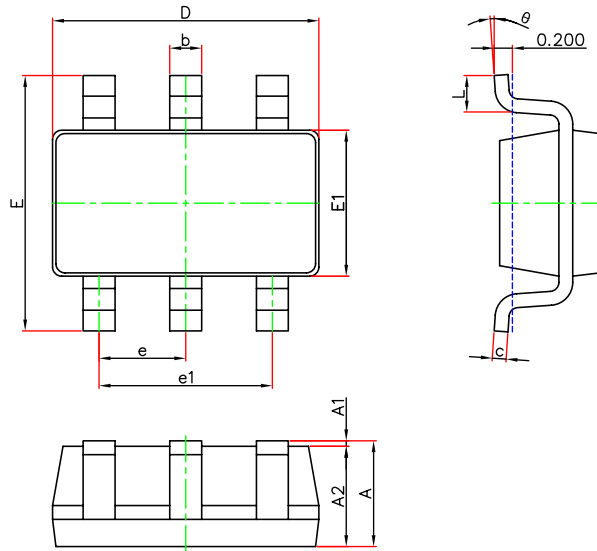
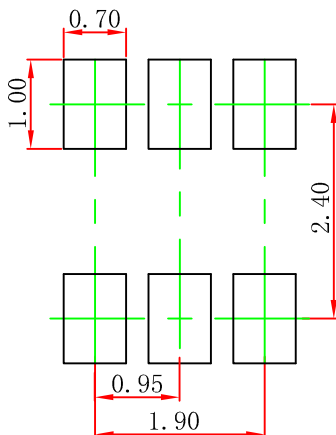


Figure 12. S switching Waveforms

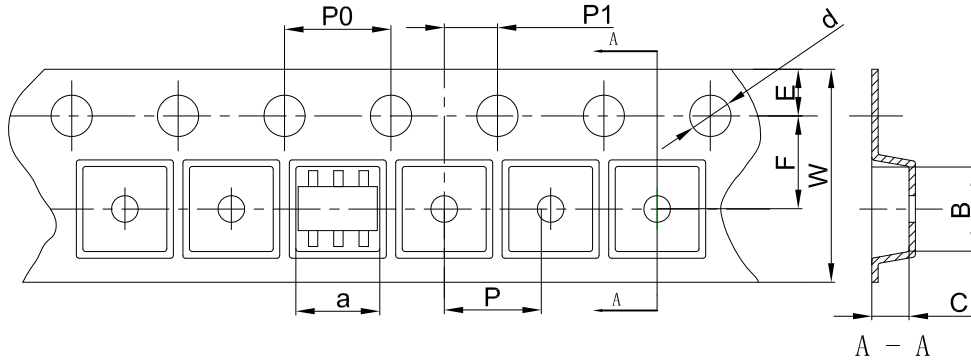


**Dual N-Channel Enhancement Mode Field Effect Transistor**
**SOT-23-6 Package Outline Dimensions**


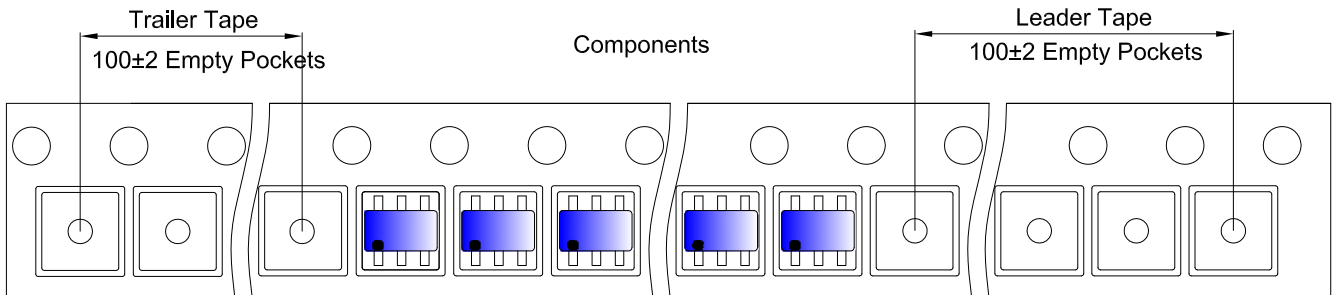
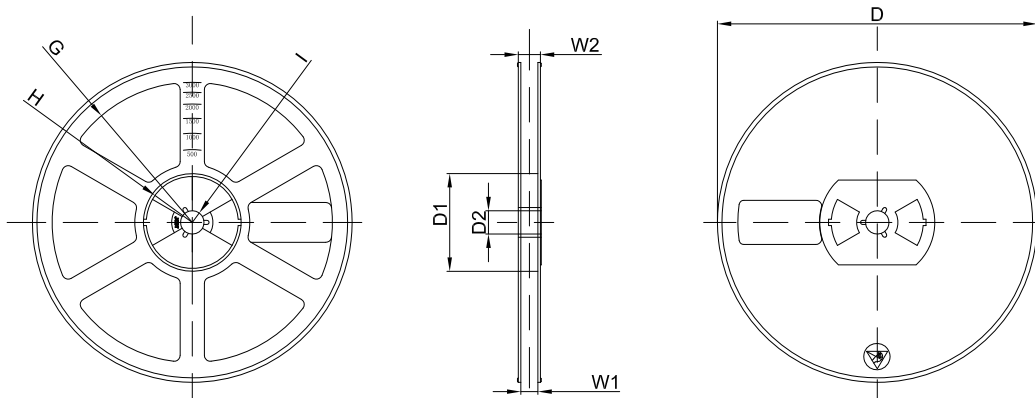
| Symbol   | Dimensions In Millimeters |       | Dimensions In Inches |       |
|----------|---------------------------|-------|----------------------|-------|
|          | Min.                      | Max.  | Min.                 | Max.  |
| A        | 1.050                     | 1.250 | 0.041                | 0.049 |
| A1       | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2       | 1.050                     | 1.150 | 0.041                | 0.045 |
| b        | 0.300                     | 0.500 | 0.012                | 0.020 |
| c        | 0.100                     | 0.200 | 0.004                | 0.008 |
| D        | 2.820                     | 3.020 | 0.111                | 0.119 |
| E1       | 1.500                     | 1.700 | 0.059                | 0.067 |
| E        | 2.650                     | 2.950 | 0.104                | 0.116 |
| e        | 0.950(BSC)                |       | 0.037(BSC)           |       |
| e1       | 1.800                     | 2.000 | 0.071                | 0.079 |
| L        | 0.300                     | 0.600 | 0.012                | 0.024 |
| $\theta$ | 0°                        | 8°    | 0°                   | 8°    |

**SOT-23-6 Suggested Pad Layout**

**Note:**

1. Controlling dimension: in millimeters
2. General tolerance:  $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

**Dual N-Channel Enhancement Mode Field Effect Transistor**
**SOT-23-6 Tape and Reel**
**SOT-23-6 Embossed Carrier Tape**


| DIMENSIONS ARE IN MILLIMETER |      |      |      |       |      |      |      |      |      |      |
|------------------------------|------|------|------|-------|------|------|------|------|------|------|
| TYPE                         | a    | B    | C    | d     | E    | F    | P0   | P    | P1   | W    |
| SOT-23-6                     | 3.17 | 3.23 | 1.37 | Ø1.50 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |
| TOLERANCE                    | ±0.1 | ±0.1 | ±0.1 | ±0.1  | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 | ±0.1 |

**SOT-23-6 Tape Leader and Trailer**

**SOT-23-6 Reel**


| DIMENSIONS ARE IN MILLIMETER |         |       |       |        |        |       |      |       |
|------------------------------|---------|-------|-------|--------|--------|-------|------|-------|
| REEL OPTION                  | D       | D1    | D2    | G      | H      | I     | W1   | W2    |
| 13" DIA                      | Ø180.00 | 60.00 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 13.10 |
| TOLERANCE                    | ±2      | ±1    | ±1    | ±1     | ±1     | ±1    | ±1   | ±1    |